2-input EXCLUSIVE-OR gate Rev. 05 — 4 July 2007

General description 1.

74AHC1G86 and 74AHCT1G86 are high-speed Si-gate CMOS devices. They provide a 2-input EXCLUSIVE-OR function.

The AHC device has CMOS input switching levels and supply voltage range 2 V to 5.5 V.

The AHCT device has TTL input switching levels and supply voltage range 4.5 V to 5.5 V.

2. **Features**

- Symmetrical output impedance
- High noise immunity
- ESD protection:
 - HBM JESD22-A114E: exceeds 2000 V
 - MM JESD22-A115-A: exceeds 200 V
 - CDM JESD22-C101C: exceeds 1000 V
- Low power dissipation
- Balanced propagation delays
- SOT353-1 and SOT753 package options
- Specified from –40 °C to +125 °C

Ordering information 3.

Table 1. **Ordering information**

Type number	Package								
	Temperature range	Name	Description	Version					
74AHC1G86GW	–40 °C to +125 °C	TSSOP5	plastic thin shrink small outline package; 5 leads; body width 1.25 mm	SOT353-1					
74AHCT1G86GW			···· ,						
74AHC1G86GV	–40 °C to +125 °C	SC-74A	plastic surface-mounted package; 5 leads	SOT753					
74AHCT1G86GV									



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4. Marking

Table 2. Marking codes	
Type number	Marking code
74AHC1G86GW	AH
74AHCT1G86GW	СН
74AHC1G86GV	A86
74AHCT1G86GV	C86

5. Functional diagram



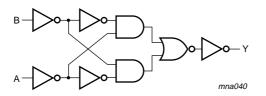
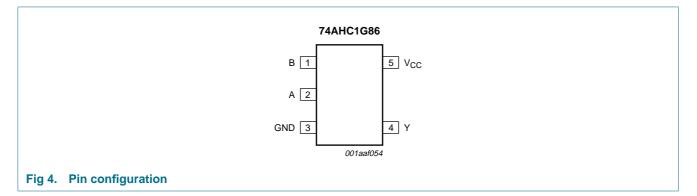


Fig 3. Logic diagram

6. Pinning information

6.1 Pinning



6.2 Pin description

Table 3.	Pin description	
Symbol	Pin	Description
В	1	data input
A	2	data input
GND	3	ground (0 V)
Y	4	data output
V _{CC}	5	supply voltage

7. Functional description

Table 4.Function table

H = *HIGH* voltage level; *L* = *LOW* voltage level

Inputs		Output
Α	В	Y
L	L	L
L	н	Н
н	L	Н
Н	Н	L

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

V _{CC} supply voltage-0.5+7.0V V_1 input voltage-0.5+7.0V I_{IK} input clamping current $V_1 < -0.5$ V-20-mA I_{OK} output clamping current $V_0 < -0.5$ V or $V_O > V_{CC} + 0.5$ V[1]- ± 20 mA I_O output current -0.5 V < $V_O < V_{CC} + 0.5$ V1- ± 20 mA I_O output current -0.5 V < $V_O < V_{CC} + 0.5$ V- ± 25 mA I_{CC} supply current-75mA I_{GND} ground current-75-mA T_{stg} storage temperature-65+150°C P_{tot} total power dissipation $T_{amb} = -40$ °C to +125 °C[2]-250mW	Symbol	Parameter	Conditions	Min	Max	Unit
InInput clamping current $V_1 < -0.5$ V -20 $-$ mAI_{OK}output clamping current $V_0 < -0.5$ V or $V_0 > V_{CC} + 0.5$ V (1) ± 20 mAI_Ooutput current -0.5 V $< V_0 < V_{CC} + 0.5$ V $ \pm 25$ mAI_{CC}supply current -0.5 V $< V_0 < V_{CC} + 0.5$ V $ \pm 25$ mAI_{GND}ground current -75 $-$ mAT_{stg}storage temperature -65 $+150$ $^{\circ}C$	-	supply voltage		-0.5	+7.0	V
IncOutput clamping current $V_O < -0.5 V \text{ or } V_O > V_{CC} + 0.5 V$ [1] - ± 20 mAI_Ooutput current $-0.5 V < V_O > V_{CC} + 0.5 V$ - ± 25 mAI_{CC}supply current-75mAI_{GND}ground current-75-mAT_{stg}storage temperature-65+150°C		input voltage		-0.5	+7.0	V
Ioroutput current $-0.5 V < V_O < V_{CC} + 0.5 V$ $ \pm 25$ mAI_{CC}supply current $-0.5 V < V_O < V_{CC} + 0.5 V$ $ \pm 25$ mAI_{GND}ground current -75 $-$ mAT_{stg}storage temperature -65 $+150$ $^{\circ}C$	I _{IK}	input clamping current	V ₁ < -0.5 V	-20	-	mA
I_{CC} supply current-75mA I_{GND} ground current-75-mA T_{stg} storage temperature-65+150°C	Ι _{ΟΚ}	output clamping current	$V_{\rm O}$ < –0.5 V or $V_{\rm O}$ > $V_{\rm CC}$ + 0.5 V	<u>[1]</u> -	±20	mA
I_{GND} ground current -75 $-$ mA T_{stg} storage temperature -65 $+150$ $^{\circ}C$	I _O	output current	$-0.5 \text{ V} < \text{V}_{\text{O}} < \text{V}_{\text{CC}} + 0.5 \text{ V}$	-	±25	mA
T_{stg} storage temperature $-65 +150$ °C	I _{CC}	supply current		-	75	mA
	I _{GND}	ground current		-75	-	mA
P_{tot} total power dissipation $T_{amb} = -40 \text{ °C to } +125 \text{ °C}$ [2] - 250 mW	T _{stg}	storage temperature		-65	+150	°C
	P _{tot}	total power dissipation	$T_{amb} = -40 \ ^{\circ}C$ to +125 $^{\circ}C$	[2] _	250	mW

[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] For both TSSOP5 and SC-74A packages: above 87.5 °C the value of P_{tot} derates linearly with 4.0 mW/K.

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9. Recommended operating conditions

Table 6. Recommended operating conditions

Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	74	AHC1G	86	74	Unit		
			Min	Тур	Max	Min	Тур	Max	
V _{CC}	supply voltage		2.0	5.0	5.5	4.5	5.0	5.5	V
VI	input voltage		0	-	5.5	0	-	5.5	V
Vo	output voltage		0	-	V_{CC}	0	-	V_{CC}	V
T _{amb}	ambient temperature		-40	+25	+125	-40	+25	+125	°C
$\Delta t / \Delta V$	input transition rise	V_{CC} = 3.3 V \pm 0.3 V	-	-	100	-	-	-	ns/V
	and fall rate	$V_{CC}=5.0~V\pm0.5~V$	-	-	20	-	-	20	ns/V

10. Static characteristics

Table 7. Static characteristics

Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		25 °C		−40 °C to +85 °C		–40 °C to +125 °C		Unit
			Min	Тур	Max	Min	Мах	Min	Мах	
For type	74AHC1G86	1								
VIH	HIGH-level	$V_{CC} = 2.0 V$	1.5	-	-	1.5	-	1.5	-	V
	input voltage	V _{CC} = 3.0 V	2.1	-	-	2.1	-	2.1	-	V
		V _{CC} = 5.5 V	3.85	-	-	3.85	-	3.85	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 2.0 V	-	-	0.5	-	0.5	-	0.5	V
		$V_{CC} = 3.0 V$	-	-	0.9	-	0.9	-	0.9	V
		$V_{CC} = 5.5 V$	-	-	1.65	-	1.65	-	1.65	V
V _{OH} HIGH-level		$V_{I} = V_{IH} \text{ or } V_{IL}$								
	output voltage	I_{O} = –50 $\mu A;$ V_{CC} = 2.0 V	1.9	2.0	-	1.9	-	1.9	-	V
		I_O = –50 $\mu A; V_{CC}$ = 3.0 V	2.9	3.0	-	2.9	-	2.9	-	V
		I_O = –50 $\mu A; V_{CC}$ = 4.5 V	4.4	4.5	-	4.4	-	4.4	-	V
		I_{O} = –4.0 mA; V_{CC} = 3.0 V	2.58	-	-	2.48	-	2.40	-	V
		I_{O} = –8.0 mA; V_{CC} = 4.5 V	3.94	-	-	3.8	-	3.70	-	V
V _{OL}	LOW-level	$V_I = V_{IH} \text{ or } V_{IL}$								
	output voltage	$I_O = 50 \ \mu\text{A}; \ V_{CC} = 2.0 \ V$	-	0	0.1	-	0.1	-	0.1	V
		$I_{O} = 50 \ \mu A; \ V_{CC} = 3.0 \ V$	-	0	0.1	-	0.1	-	0.1	V
		$I_O = 50 \ \mu\text{A}; \ V_{CC} = 4.5 \ V$	-	0	0.1	-	0.1	-	0.1	V
		I_{O} = 4.0 mA; V_{CC} = 3.0 V	-	-	0.36	-	0.44	-	0.55	V
		I_{O} = 8.0 mA; V_{CC} = 4.5 V	-	-	0.36	-	0.44	-	0.55	V
l _l	input leakage current	V _I = 5.5 V or GND; V _{CC} = 0 V to 5.5 V	-	-	0.1	-	1.0	-	2.0	μΑ
I _{CC}	supply current		-	-	1.0	-	10	-	40	μΑ
CI	input capacitance		-	1.5	10	-	10	-	10	pF

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Symbol	Parameter	Conditions		25 °C		_40 °C	to +85 °C	–40 °C to +125 °C		Unit
			Min	Тур	Max	Min	Max	Min	Max	1
For type	74AHCT1G86									
V _{IH}	HIGH-level input voltage	V_{CC} = 4.5 V to 5.5 V	2.0	-	-	2.0	-	2.0	-	V
V _{IL}	LOW-level input voltage	V_{CC} = 4.5 V to 5.5 V	-	-	0.8	-	0.8	-	0.8	V
V _{OH}	HIGH-level	V_{I} = V_{IH} or $V_{\text{IL}};$ V_{CC} = 4.5 V								
	output voltage	I _O = -50 μA	4.4	4.5	-	4.4	-	4.4	-	V
		I _O = -8.0 mA	3.94	-	-	3.8	-	3.70	-	V
V _{OL} LOW-level	V_{I} = V_{IH} or $V_{IL};V_{CC}$ = 4.5 V									
	output voltage	I _O = 50 μA	-	0	0.1	-	0.1	-	0.1	V
		I _O = 8.0 mA	-	-	0.36	-	0.44	-	0.55	V
I	input leakage current	$V_1 = 5.5 V \text{ or GND};$ $V_{CC} = 0 V \text{ to } 5.5 V$	-	-	0.1	-	1.0	-	2.0	μΑ
I _{CC}	supply current	$V_I = V_{CC} \text{ or GND}; I_O = 0 \text{ A};$ $V_{CC} = 5.5 \text{ V}$	-	-	1.0	-	10	-	40	μΑ
ΔI_{CC}	additional supply current	per input pin; $V_I = 3.4 V$; other inputs at V_{CC} or GND; $I_O = 0 A$; $V_{CC} = 5.5 V$	-	-	1.35	-	1.5	-	1.5	mA
CI	input capacitance		-	1.5	10	-	10	-	10	pF

11. Dynamic characteristics

Table 8. Dynamic characteristics

GND = 0 V; $t_r = t_f = \le 3.0$ ns. For waveform see <u>Figure 5</u>. For test circuit see <u>Figure 6</u>.

			-								
Symbol	Parameter	Conditions			25 °C		-40 °C ∱	to +85 °C	−40 °C to +125 °C		Unit
				Min	Тур	Max	Min	Max	Min	Max	
For type	74AHC1G86										
t _{pd} propagation delay		A and B to Y	<u>[1]</u>								
	V_{CC} = 3.0 V to 3.6 V	[2]									
		C _L = 15 pF		-	4.0	11.0	1.0	13.0	1.0	14.0	ns
		C _L = 50 pF		-	5.8	14.5	1.0	16.5	1.0	18.5	ns
		V_{CC} = 4.5 V to 5.5 V	[3]								
		C _L = 15 pF		-	3.4	6.8	1.0	8.0	1.0	8.5	ns
		C _L = 50 pF		-	4.9	8.8	1.0	10.0	1.0	11.5	ns
C _{PD}	power dissipation capacitance	per buffer; $C_L = 50 \text{ pF}; \text{ f} = 1 \text{ MHz};$ $V_I = \text{GND to } V_{CC}$	<u>[4]</u>	-	9	-	-	-	-	-	pF

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GND = 0	$V; t_r = t_f = \leq 3.$	0 ns. For waveform see <mark>Fig</mark>	gure 5.	For te	st circu	it see <mark>F</mark>	igure 6.				
Symbol	Parameter	Conditions		25 °C			−40 °C to +85 °C		−40 °C t	o +125 °C	Unit
				Min	Тур	Max	Min	Max	Min	Max	
For type	74AHCT1G8	6									
t _{pd}	propagation delay	A and B to Y	[1]								
		V_{CC} = 4.5 V to 5.5 V	[3]								
		C _L = 15 pF		-	3.5	6.9	1.0	8.0	1.0	9.0	ns
		C _L = 50 pF		-	5.0	7.9	1.0	9.0	1.0	10.5	ns
C _{PD}	power dissipation capacitance	per buffer; $C_L = 50 \text{ pF}; f = 1 \text{ MHz};$ $V_I = \text{GND to } V_{CC}$	<u>[4]</u>	-	11	-	-	-	-	-	pF

Table 8. Dynamic characteristics ... continued

[1] t_{pd} is the same as t_{PLH} and t_{PHL} .

[2] Typical values are measured at V_{CC} = 3.3 V.

[3] Typical values are measured at V_{CC} = 5.0 V.

[4] C_{PD} is used to determine the dynamic power dissipation P_D (μW).

 $P_D = C_{PD} \times V_{CC}^2 \times f_i + \sum (C_L \times V_{CC}^2 \times f_o)$ where:

 f_i = input frequency in MHz;

 $f_o = output frequency in MHz;$

 C_L = output load capacitance in pF;

V_{CC} = supply voltage in Volts.

12. Waveforms

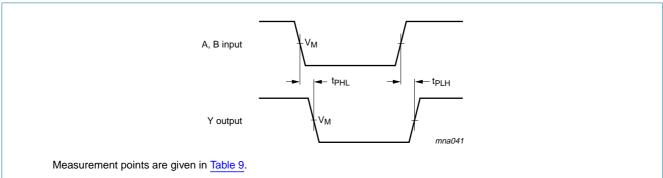


Fig 5. The input (A and B) to output (Y) propagation delays

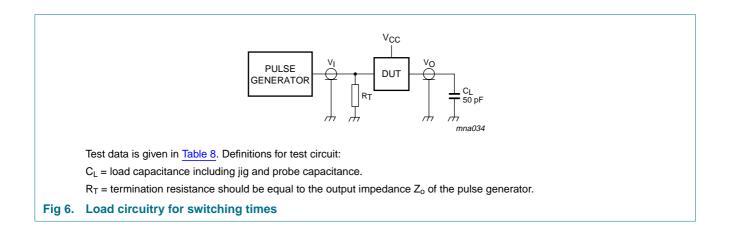
Table 9. **Measurement points**

Туре	Input	Output	
	VI	V _M	V _M
74AHC1G86	GND to V _{CC}	$0.5 \times V_{CC}$	$0.5 \times V_{CC}$
74AHCT1G86	GND to 3.0 V	1.5 V	$0.5 imes V_{CC}$

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74AHC1G86; 74AHCT1G86

2-input EXCLUSIVE-OR gate



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13. Package outline

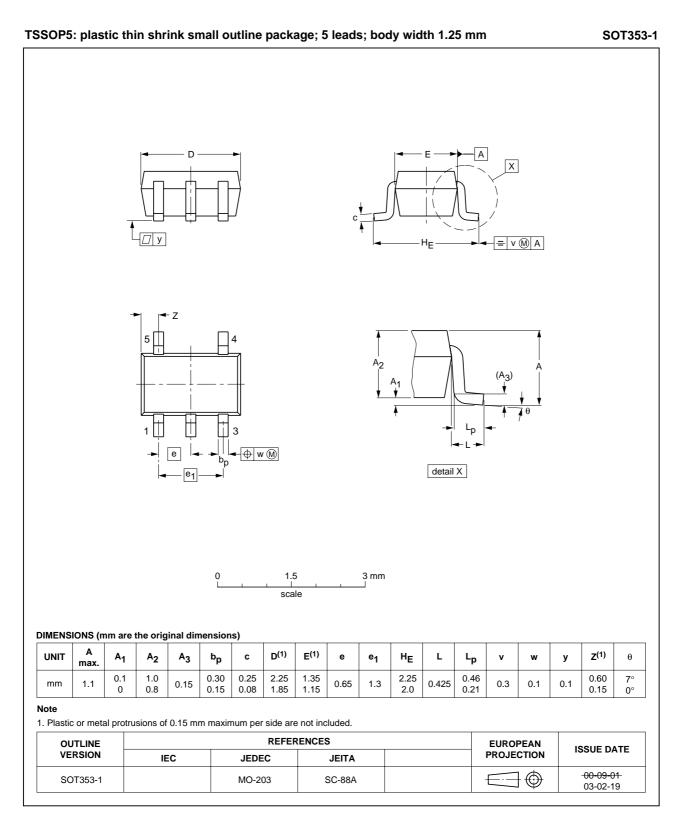


Fig 7. Package outline SOT353-1 (TSSOP5)

2-input EXCLUSIVE-OR gate

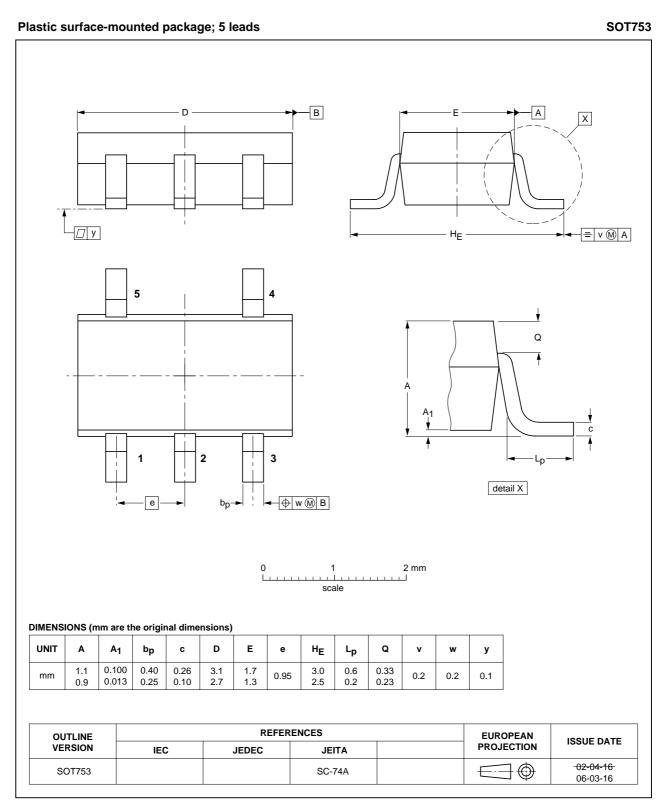


Fig 8. Package outline SOT753 (SC-74A)

2-input EXCLUSIVE-OR gate

14. Abbreviations

Table 10.	Abbreviations
Acronym	Description
CDM	Charged Device Model
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
MM	Machine Model
TTL	Transistor-Transistor Logic

15. Revision history

Table 11.	Revision	history
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	· ·			
Document ID	Release date	Data sheet status	Change notice	Supersedes
74AHC_AHCT1G86_5	20070704	Product data sheet	-	74AHC_AHCT1G86_4
Modifications:		f this data sheet has been rede NXP Semiconductors.	esigned to comply w	ith the new identity
	 Legal texts have 	ave been adapted to the new o	company name wher	e appropriate.
	 Package SOT 	T353 changed to SOT353-1 in	Section 3 and Section	<u>on 13</u> .
	 Quick referen 	nce data and Soldering section	s removed.	
74AHC_AHCT1G86_4	20020606	Product specification	-	74AHC_AHCT1G86_3
74AHC_AHCT1G86_3	20020218	Product specification	-	74AHC_AHCT1G86_2
74AHC_AHCT1G86_2	20010406	Product specification	-	74AHC1G_AHCT1G86_1
74AHC1G_AHCT1G86_1	19990920	Product specification	-	-

16. Legal information

16.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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2-input EXCLUSIVE-OR gate

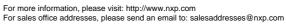
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